NCE Automotive N-Channel Super Trench II Power MOSFET

Description

The series of devices uses **Super Trench II** technology that is uniquely optimized to provide the most efficient high frequency switching performance. Both conduction and switching power losses are minimized due to an extremely low combination of $R_{\text{DS(ON)}}$ and Q_g . This device is ideal for high-frequency switching and synchronous rectification.

Application

- Automotive application
- DC/DC Converter
- Ideal for high-frequency switching and synchronous rectification

General Features

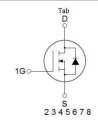
V_{DS} =85V,I_D =210A

 $R_{DS(ON)}$ =2.65m Ω , typical @ V_{GS} =10V

- Excellent gate charge x R_{DS(on)} product(FOM)
- Very low on-resistance R_{DS(on)}
- 175 °C operating temperature
- Pb-free lead plating
- 100% UIS tested
- 100% ΔVds tested
- AEC-Q101 qualified

TOLL-8L





Schematic Diagram

Package Marking and Ordering Information

Device Marking	Device	Device Package	Reel Size	Tape width	Quantity
AP030N85LL	NCEAP030N85LL	TOLL-8L	-	-	-

Absolute Maximum Ratings (T_C=25 ℃unless otherwise noted)

Parameter	Symbol	Limit	Unit
Drain-Source Voltage	V _{DS}	85	V
Gate-Source Voltage	Vgs	±20	V
Drain Current-Continuous	I _D	210	Α
Drain Current-Continuous(T _C =100 °C)	I _D (100℃)	160	А
Pulsed Drain Current	I _{DM}	840	Α
Maximum Power Dissipation	P _D	300	W
Derating factor		2.0	W/℃
Single pulse avalanche energy (Note 1)	E _{AS}	1350	mJ
Operating Junction and Storage Temperature Range	T _J ,T _{STG}	-55 To 175	$^{\circ}\mathbb{C}$

Thermal Characteristic

Parameter	Symbol	Тур	Max	Unit
Thermal Resistance, Junction-to-Case	R _{eJC}	0.32	0.5	°C/W

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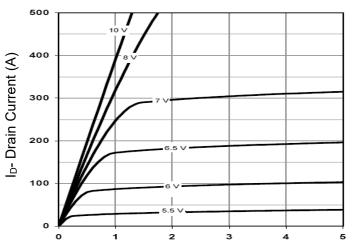
Electrical Characteristics (T_C=25 °C unless otherwise noted)

Parameter	Symbol	Condition	Min	Тур	Max	Unit
Off Characteristics				'		
Drain-Source Breakdown Voltage	BV _{DSS}	V _{GS} =0V I _D =250µA	85	-	-	V
Zero Gate Voltage Drain Current	I _{DSS}	V _{DS} =85V,V _{GS} =0V	-	-	1	μA
Gate-Body Leakage Current	I _{GSS}	V_{GS} =±20V, V_{DS} =0V	-	-	±100	nA
On Characteristics						
Gate Threshold Voltage	V _{GS(th)}	$V_{DS}=V_{GS},I_{D}=250\mu A$	2.0	3.0	4.0	V
Drain-Source On-State Resistance	R _{DS(ON)}	V _{GS} =10V, I _D =20A	-	2.65	3.0	mΩ
Gate resistance	R _G	F=1.0MHz	0.2	2.0	4.0	Ω
Forward Transconductance	g FS	V _{DS} =5V,I _D =20A	-	90	-	S
Dynamic Characteristics				•		
Input Capacitance	C _{lss}	\/ 40\/\/ 0\/	-	7200	-	pF
Output Capacitance	Coss	V_{DS} =40V, V_{GS} =0V, F=1.0MHz	-	1100	-	pF
Reverse Transfer Capacitance	C _{rss}	F=1.UIVIH2	-	24	-	pF
Switching Characteristics (Note 2)				•		
Turn-on Delay Time	t _{d(on)}		-	21	-	nS
Turn-on Rise Time	t _r	V_{DD} =40 V , I_{D} =20 A	-	12.5	-	nS
Turn-Off Delay Time	t _{d(off)}	V_{GS} =10 V , R_{G} =1.6 Ω	-	48	-	nS
Turn-Off Fall Time	t _f		-	12	-	nS
Total Gate Charge	Qg	V 40V L 00A	-	115	-	nC
Gate-Source Charge	Qgs	V _{DS} =40V,I _D =20A,	-	39	-	nC
Gate-Drain Charge	Q _{gd}	V _{GS} =10V	-	32	-	nC
Drain-Source Diode Characteristics						
Diode Forward Voltage	V _{SD}	V _{GS} =0V,I _S =20A	-	-	1.2	V
Diode Forward Current	Is		-	-	210	Α
Reverse Recovery Time	t _{rr}	T _J = 25°C, I _F = 20A	-	80	-	nS
Reverse Recovery Charge	Qrr	di/dt = 100A/μs	_	147	_	nC

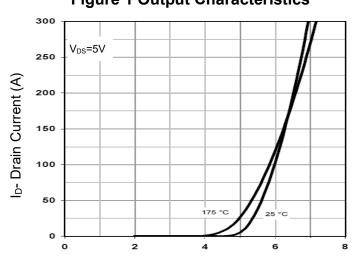
Notes:

- 1. EAS condition : Tj=25 $^{\circ}\text{C}\,\text{,V}_\text{DD}\text{=}40\text{V}\text{,V}_\text{G}\text{=}10\text{V}\text{,L=}0.5\text{mH}\text{,Rg=}25\Omega$
- 2. Guaranteed by design, not subject to production
- 3. These curves are based on the junction-to-case thermal impedance which is measured with the device mounted to a large heatsink, assuming a maximum junction temperature of T_{J(MAX)}=175°C. The SOA curve provides a single pulse rating.

Typical Electrical and Thermal Characteristics



Vds Drain-Source Voltage (V)
Figure 1 Output Characteristics



Vgs Gate-Source Voltage (V)

Figure 2 Transfer Characteristics

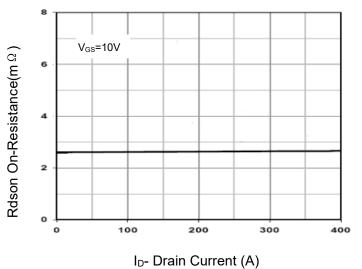
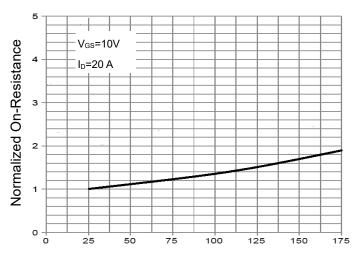
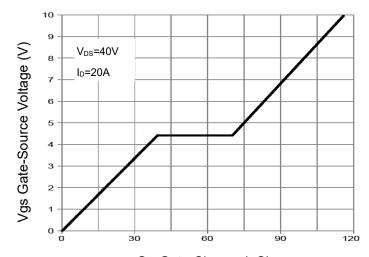


Figure 3 Rdson- Drain Current



T_J-Junction Temperature(°C)

Figure 4 Rdson-Junction Temperature



Qg Gate Charge (nC)

Figure 5 Gate Charge

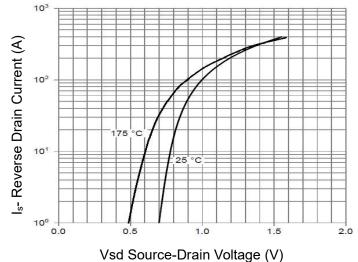
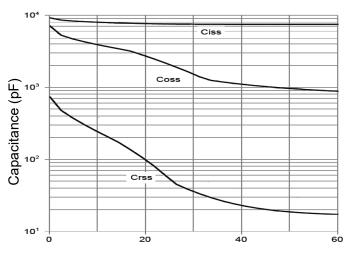


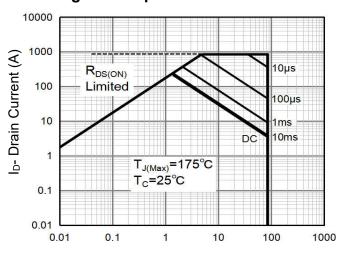
Figure 6 Source- Drain Diode Forward





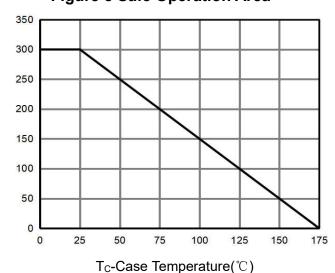
Vds Drain-Source Voltage (V)

Figure 7 Capacitance vs Vds



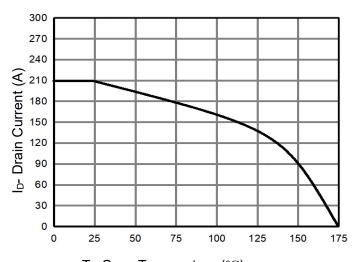
Vds Drain-Source Voltage (V)

Figure 8 Safe Operation Area(Note 3)



Power Dissipation (W)

Figure 9 Power De-rating



 $T_{\text{C}}\text{-}\text{Case}$ Temperature (°C)

Figure 10 Current De-rating

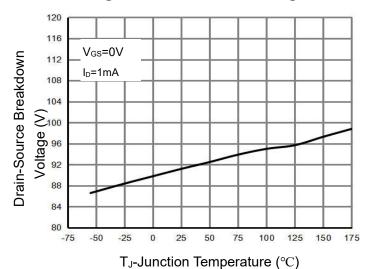
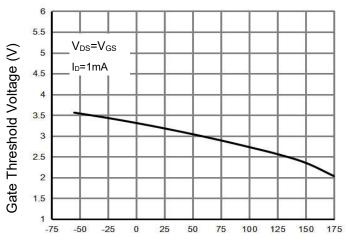


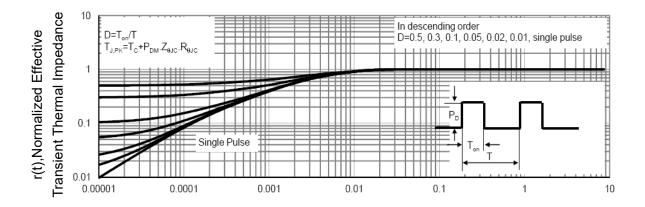
Figure 11 BV_{DSS}-Junction Temperature



T_J-Junction Temperature (°C)

Figure 12 V_{GS(th)}-Junction Temperature



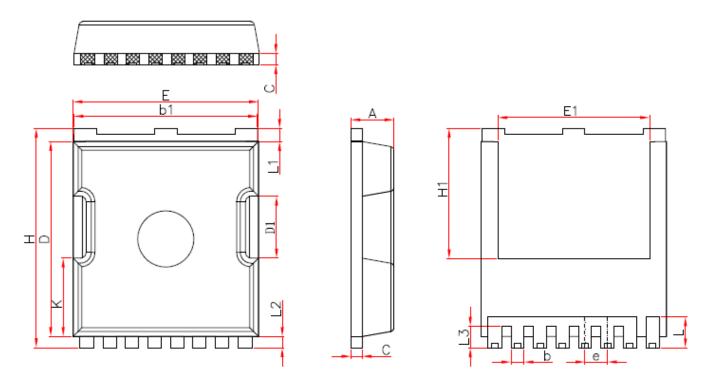


Square Wave Pluse Duration(sec)

Figure 13 Normalized Maximum Transient Thermal Impedance



TOLL Package Information

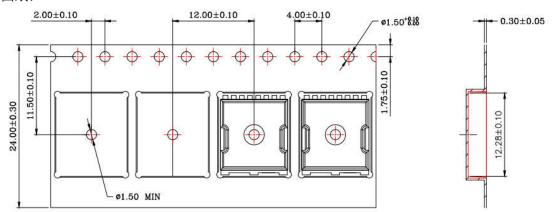


Symbol	Millimeters				
838	Min.	Nom.	Max.		
A	2.20	2.30	2.40		
b	0.65	0.75	0.85		
b1	9.70	9.80	9.90		
C	0.50	0.60	0.70		
D	10.30	10.40	10.50		
D1	3.15	3.3	3.45		
Е	9.70	9.90	10.10		
E1	8.00	8.10	8.20		
е	1.10	1.20	1.30		
Н	11.6	11.7	11.8		
H1	6.85	6.95	7.05		
K	4.08	4.18	4.28		
L	1.60	1.65	2.10		
L1	0.60	0.70	0.80		
L2	0.50	0.60	0.70		
L3	1.05	1.20	1.30		

-10.50±0.10

Package information

一、载带图纸:



Notes:

- 1. All dimensions are in mm.
- 2. Material: Black Conductive Polystyrene Alloy
- 3. 10 sprocket hole pitch cumulative tolerance ± 0.20 mm.
- 4. Carrier camber is within 1 mm in 250 mm.
- 5. Packing length per 19" reel: 196.0 Meters.
- 6. There must not be foreign body adhesion and the state of the surface must be excellent.
- 7.Surface Resistance 1X10E5~1x10E11 OHMS/SQ

二、包装信息表 (满箱信息)

封装形式	包装方式	盘尺寸	只/盘	盘/内盒	只/内盒	内盒/箱	只/箱
TOLL	编带	13寸	2000	1	2000	8	16000

http://www.ncepower.com

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